

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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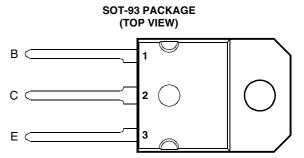






BOURNS®

- Designed for Complementary Use with the TIP33 Series
- 80 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- 15 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

1

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT
	TIP34		-80	
Collector-base voltage (I _F = 0)	TIP34A	V	-100	V
Collector-base voltage (IE = 0)	TIP34B	V _{СВО}	-120	٧
	TJP34C		-140	
	TIP34		-40	
Collector-emitter voltage (I _B = 0)	TIP34A	V	-60	V
	TIP34B	V _{CEO}	-80	V
	TIP34C		-100	
Emitter-base voltage		V _{EBO}	-5	V
Continuous collector current		I _C	-10	Α
Peak collector current (see Note 1)		I _{CM}	-15	Α
Continuous base current		I _B	-3	Α
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			80	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note	3)	P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		½Ll _C ²	62.5	mJ
Operating junction temperature range		T _j	-65 to +150	°C
Storage temperature range		T _{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

- 2. Derate linearly to 150°C case temperature at the rate of 0.64 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITION	ONS	MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA (see Note 5)	I _B = 0	TIP34 TIP34A TIP34B TIP34C	-40 -60 -80 -100			V
I _{CES}	Collector-emitter cut-off current	$V_{CE} = -80 \text{ V}$ $V_{CE} = -100 \text{ V}$ $V_{CE} = -120 \text{ V}$ $V_{CE} = -140 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP34 TIP34A TIP34B TIP34C			-0.4 -0.4 -0.4 -0.4	mA
I _{CEO}	Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_{B} = 0$ $I_{B} = 0$	TIP34/34A TIP34B/34C			-0.7 -0.7	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0				-1	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = -4 V$ $V_{CE} = -4 V$	$I_{C} = -1A$ $I_{C} = -3 A$	(see Notes 5 and 6)	40 20		100	
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = -0.3 \text{ A}$ $I_B = -2.5 \text{ A}$	$I_{\rm C} = -3 {\rm A}$ $I_{\rm C} = -10 {\rm A}$	(see Notes 5 and 6)			-1 -4	V
V _{BE}	Base-emitter voltage	$V_{CE} = -4 V$ $V_{CE} = -4 V$	$I_{\rm C} = -3 \text{ A}$ $I_{\rm C} = -10 \text{ A}$	(see Notes 5 and 6)			-1.6 -3	٧
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.5 A	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.5 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, t₀ = 300 µs, duty cycle ≤ 2%.

thermal characteristics

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.56	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = -6 A	$I_{B(on)} = -0.6 \text{ A}$	$I_{B(off)} = 0.6 A$		0.4		μs
t _{off}	Turn-off time	$V_{BE(off)} = 4 V$	$R_L = 5 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		0.7		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

1000

100

10

-0.01

h_{FE} - DC Current Gain

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN VS COLLECTOR CURRENT $V_{CE} = -4 V$ $V_{CE} = 25^{\circ}C$ $V_{DE} = 300 \mu s$, duty cycle < 2%

COLLECTOR-EMITTER SATURATION VOLTAGE

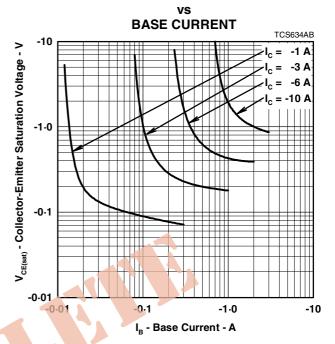


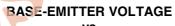
Figure 1.

I_c - Collector Current - A

-1.0

-0.1

Figure 2.



-10

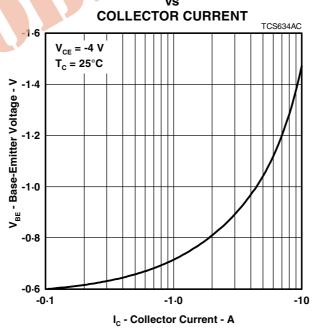
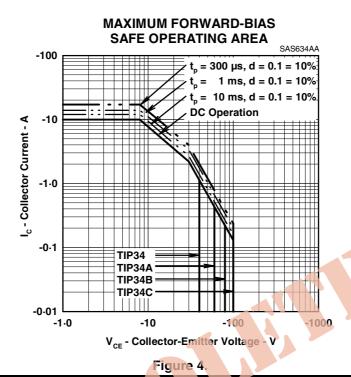


Figure 3.

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

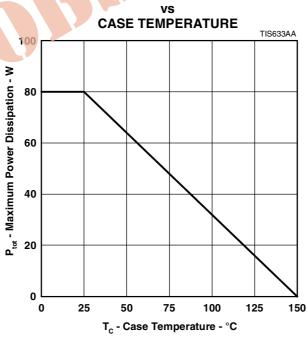


Figure 5.